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April 2015

FDP083N15A N-Channel PowerTrench[®] MOSFET 150 V, 117 A, 8.3 mΩ

Features

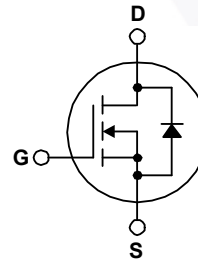
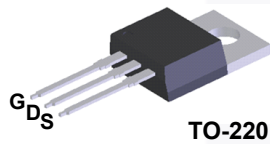
- $R_{DS(on)} = 6.85 \text{ m}\Omega$ (Typ.) @ $V_{GS} = 10 \text{ V}$, $I_D = 75 \text{ A}$
- Fast Switching Speed
- Low Gate Charge, $Q_G = 64.5 \text{ nC}$ (Typ.)
- High Performance Trench Technology for Extremely Low $R_{DS(on)}$
- High Power and Current Handling Capability
- RoHS Compliant

Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's PowerTrench[®] process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- Synchronous Rectification for ATX / Server / Telecom PSU
- Battery Protection Circuit
- Motor Drives and Uninterruptible Power Supplies
- Micro Solar Inverter



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

| Symbol | Parameter | FDP083N15A_F102 | Unit |
|----------------|--|---|------------------|
| V_{DSS} | Drain to Source Voltage | 150 | V |
| V_{GSS} | Gate to Source Voltage | - DC | ± 20 |
| | | - AC ($f > 1 \text{ Hz}$) | ± 30 |
| I_D | Drain Current | - Continuous ($T_C = 25^\circ\text{C}$, Silicon Limited) | 117 |
| | | - Continuous ($T_C = 100^\circ\text{C}$, Silicon Limited) | 83 |
| I_{DM} | Drain Current | - Pulsed (Note 1) | 468 |
| E_{AS} | Single Pulsed Avalanche Energy | (Note 2) | 542 |
| dv/dt | Peak Diode Recovery dv/dt | (Note 3) | 6 |
| P_D | Power Dissipation | ($T_C = 25^\circ\text{C}$) | 294 |
| | | - Derate Above 25°C | 1.96 |
| T_J, T_{STG} | Operating and Storage Temperature Range | -55 to +175 | $^\circ\text{C}$ |
| T_L | Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds | 300 | $^\circ\text{C}$ |

Thermal Characteristics

| Symbol | Parameter | FDP083N15A_F102 | Unit |
|-----------------|---|-----------------|---------------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case, Max. | 0.51 | $^\circ\text{C}/\text{W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient, Max. | 62.5 | |

FDP083N15A — N-Channel PowerTrench[®] MOSFET

Package Marking and Ordering Information

| Part Number | Top Mark | Package | Packing Method | Reel Size | Tape Width | Quantity |
|-----------------|------------|---------|----------------|-----------|------------|----------|
| FDP083N15A_F102 | FDP083N15A | TO-220 | Tube | N/A | N/A | 50 units |

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|--------|-----------|-----------------|------|------|------|------|
|--------|-----------|-----------------|------|------|------|------|

Off Characteristics

| | | | | | | |
|--------------------------------|---|---|-----|------|-----------|---------------------------|
| BV_{DSS} | Drain to Source Breakdown Voltage | $I_D = 250 \mu\text{A}, V_{GS} = 0 \text{ V}, T_C = 25^\circ\text{C}$ | 150 | - | - | V |
| $\Delta BV_{DSS} / \Delta T_J$ | Breakdown Voltage Temperature Coefficient | $I_D = 250 \mu\text{A}$, Referenced to 25°C | - | 0.08 | - | $\text{V}/^\circ\text{C}$ |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 120 \text{ V}, T_C = 150^\circ\text{C}$ | - | - | 1 500 | μA |
| I_{GSS} | Gate to Body Leakage Current | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ | - | - | ± 100 | nA |

On Characteristics

| | | | | | | |
|--------------|--------------------------------------|---|-----|------|------|------------------|
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{GS} = V_{DS}, I_D = 250 \mu\text{A}$ | 2.0 | - | 4.0 | V |
| $R_{DS(on)}$ | Static Drain to Source On Resistance | $V_{GS} = 10 \text{ V}, I_D = 75 \text{ A}$ | - | 6.85 | 8.30 | $\text{m}\Omega$ |
| g_{FS} | Forward Transconductance | $V_{DS} = 10 \text{ V}, I_D = 75 \text{ A}$ | - | 139 | - | S |

Dynamic Characteristics

| | | | | | | |
|--------------|-----------------------------------|--|----------|------|------|----------|
| C_{iss} | Input Capacitance | $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1 \text{ MHz}$ | - | 4645 | 6040 | pF |
| C_{oss} | Output Capacitance | | - | 1445 | 1880 | pF |
| C_{rss} | Reverse Transfer Capacitance | | - | 100 | - | pF |
| C_{iss} | Input Capacitance | $V_{DS} = 7.5 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1 \text{ MHz}$ | - | 4570 | 6040 | pF |
| C_{oss} | Output Capacitance | | - | 460 | 1880 | pF |
| C_{rss} | Reverse Transfer Capacitance | | - | 20 | - | pF |
| $Q_{g(tot)}$ | Total Gate Charge at 10V | $V_{DS} = 120 \text{ V}, I_D = 75 \text{ A},$ $V_{GS} = 10 \text{ V}$ | - | 64.5 | 84 | nC |
| Q_{gs} | Gate to Source Gate Charge | | - | 19.1 | - | nC |
| Q_{gs2} | Gate Charge Threshold to Plateau | | - | 8.7 | - | nC |
| Q_{gd} | Gate to Drain "Miller" Charge | | (Note 4) | - | 13.5 | - |
| ESR | Equivalent Series Resistance(G-S) | $f = 1 \text{ MHz}$ | - | 2.5 | - | Ω |

Switching Characteristics

| | | | | | | |
|--------------|---------------------|---|----------|----|-----|----|
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DD} = 75 \text{ V}, I_D = 75 \text{ A},$ $V_{GS} = 10 \text{ V}, R_G = 4.7 \Omega$ | - | 22 | 54 | ns |
| t_r | Turn-On Rise Time | | - | 58 | 126 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time | | - | 61 | 132 | ns |
| t_f | Turn-Off Fall Time | | (Note 4) | - | 26 | 62 |

Drain-Source Diode Characteristics

| | | | | | | |
|----------|--|---|---|-----|------|----|
| I_S | Maximum Continuous Drain to Source Diode Forward Current | - | - | 117 | A | |
| I_{SM} | Maximum Pulsed Drain to Source Diode Forward Current | - | - | 468 | A | |
| V_{SD} | Drain to Source Diode Forward Voltage | $V_{GS} = 0 \text{ V}, I_{SD} = 75 \text{ A}$ | - | - | 1.25 | V |
| t_{rr} | Reverse Recovery Time | $V_{GS} = 0 \text{ V}, I_{SD} = 75 \text{ A},$ $di_F/dt = 100 \text{ A}/\mu\text{s}$ | - | 96 | - | ns |
| Q_{rr} | Reverse Recovery Charge | | - | 268 | - | nC |

Notes:

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. Starting $T_J = 25^\circ\text{C}$, $L = 3 \text{ mH}$, $I_{SD} = 19 \text{ A}$.
3. $I_{SD} \leq 75 \text{ A}$, $di/dt \leq 200 \text{ A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.
4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

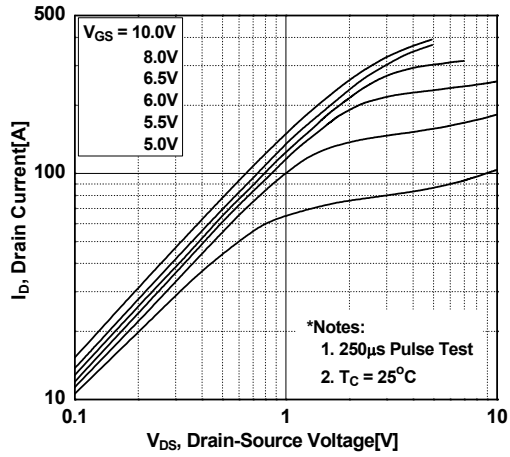


Figure 2. Transfer Characteristics

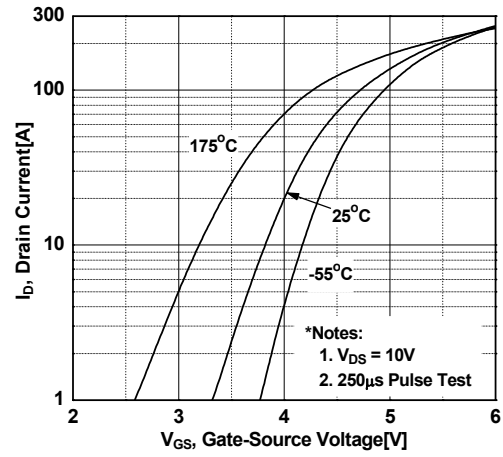


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

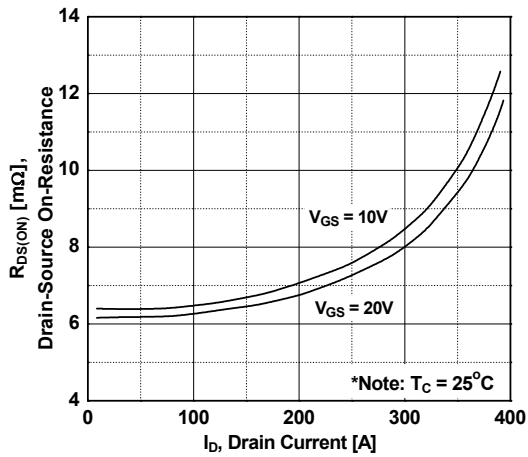


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

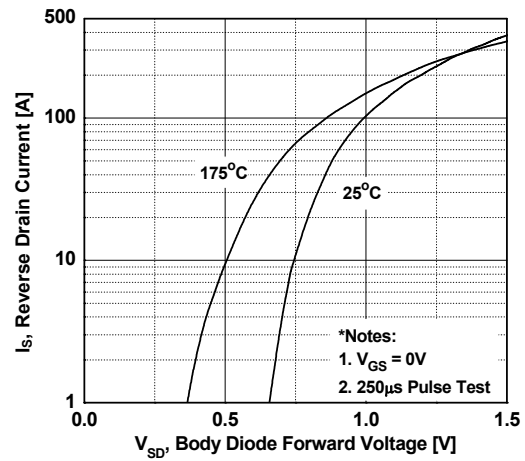


Figure 5. Capacitance Characteristics

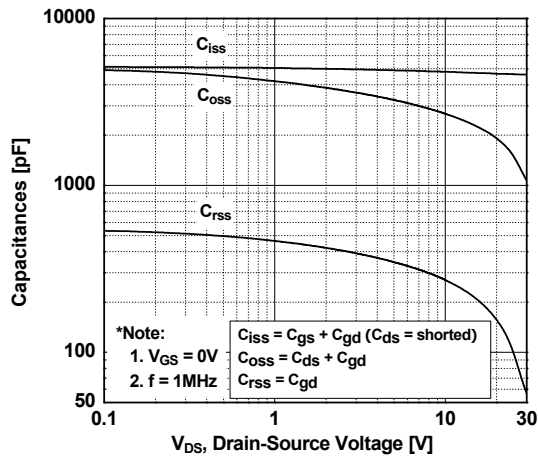
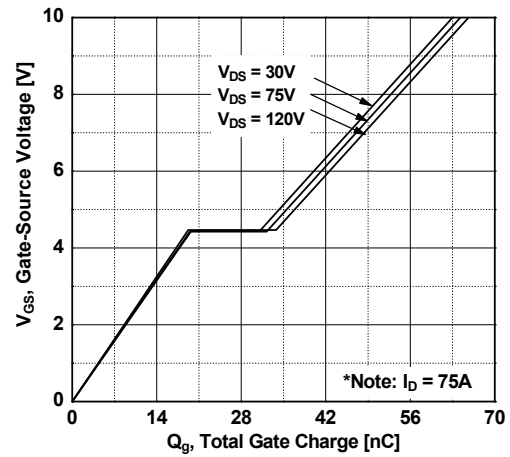


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

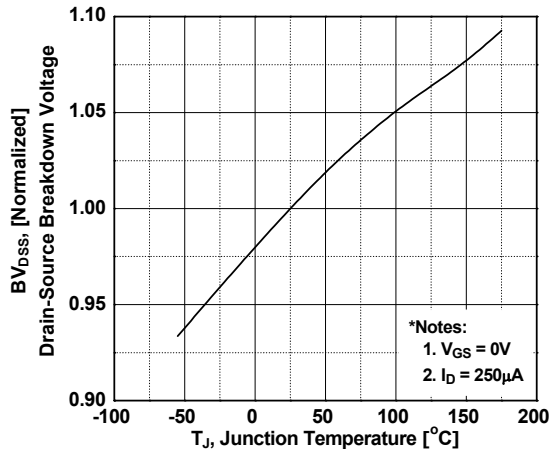


Figure 8. On-Resistance Variation vs. Temperature

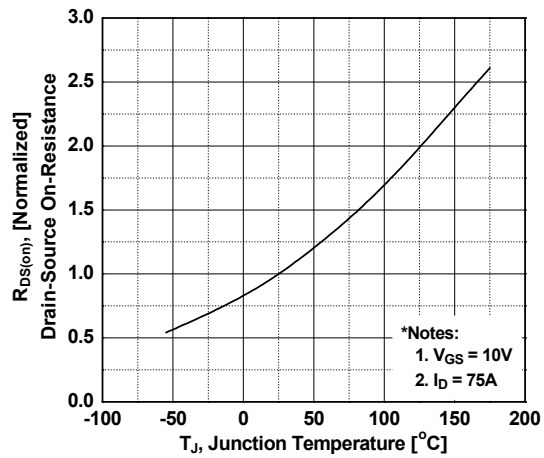


Figure 9. Maximum Safe Operating Area

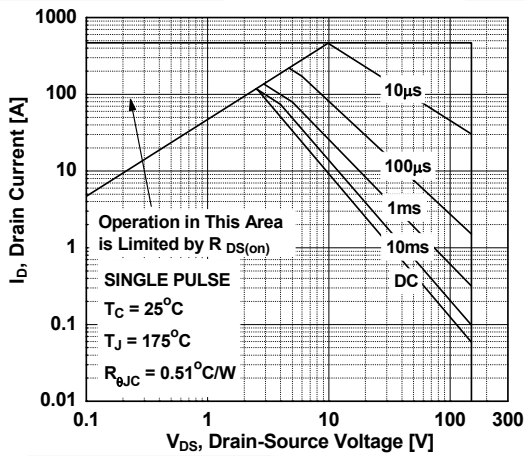


Figure 10. Maximum Drain Current vs. Case Temperature

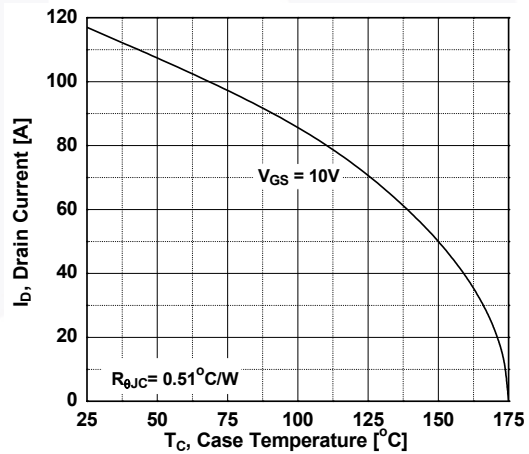
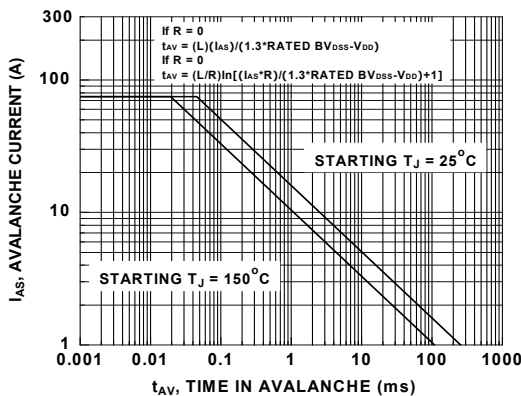


Figure 11. Unclamped Inductive Switching Capability



Typical Performance Characteristics (Continued)

Figure 12. Transient Thermal Response Curve

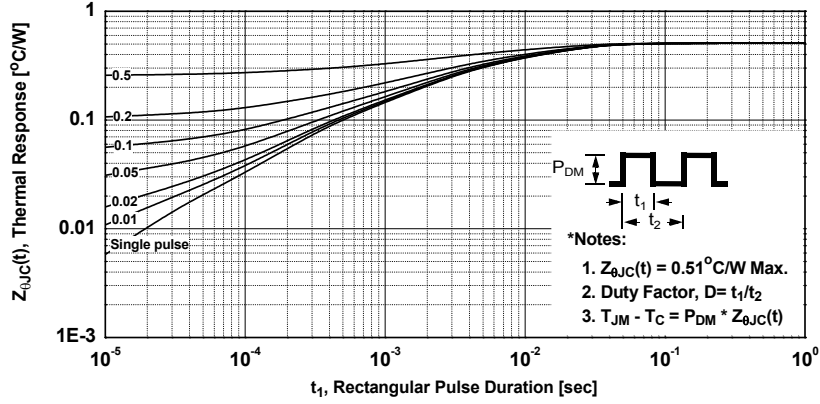




Figure 13. Gate Charge Test Circuit & Waveform



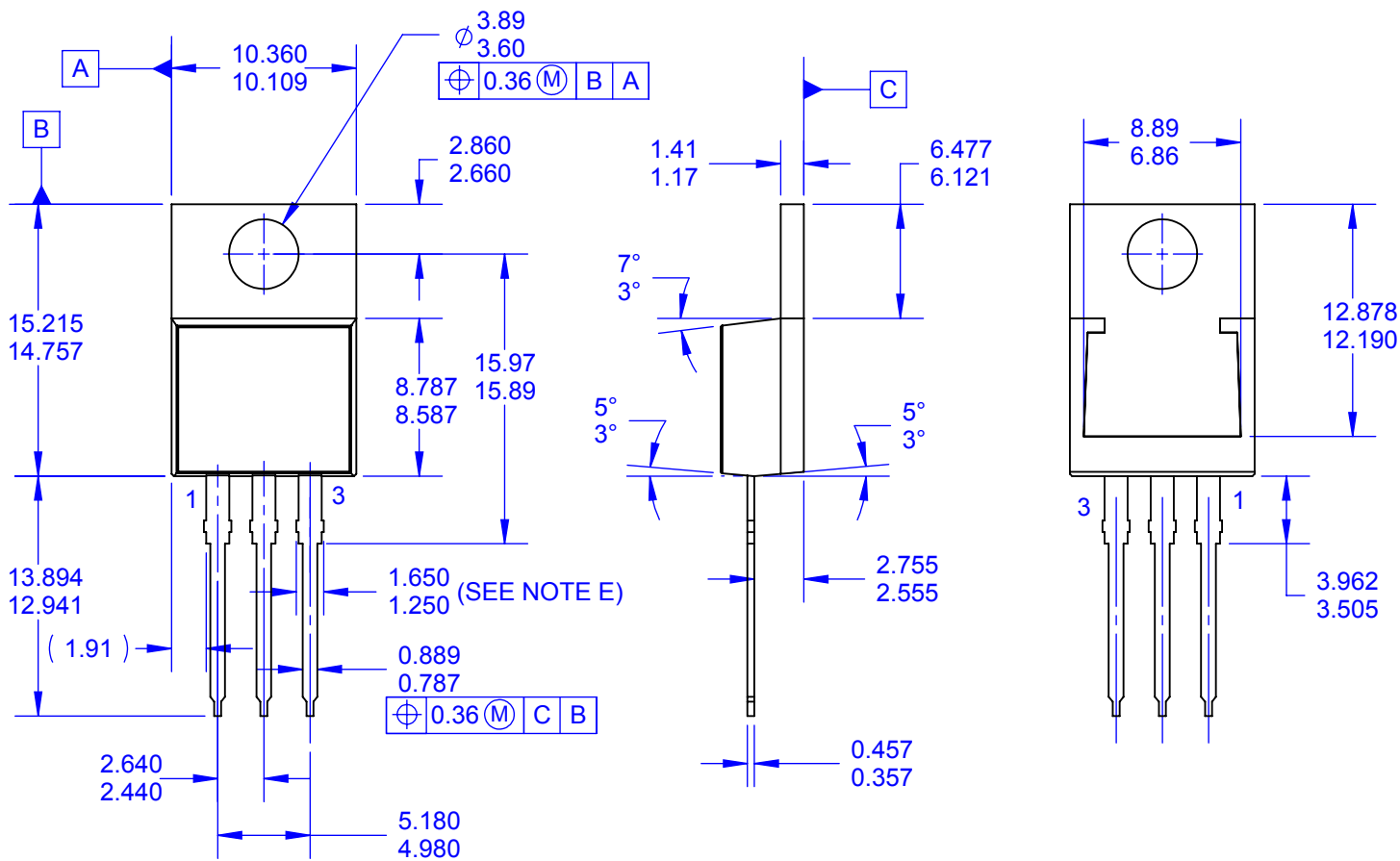
Figure 14. Resistive Switching Test Circuit & Waveforms



Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms



Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms



NOTES:

- A. PACKAGE REFERENCE: JEDEC TO220 VARIATION AB
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSION AND TOLERANCE AS PER ASME Y14.5-2009.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. MAX WIDTH FOR F102 DEVICE = 1.35mm.
- F. DRAWING FILE NAME: TO220T03REV4.
- G. FAIRCHILD SEMICONDUCTOR.

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